CLAIMS

1. A dielectric ceramic composition comprising a main component including 53.00 to 80.00mol % magnesium oxide converted to MgO, 19.60 to 47.00mol % titanium oxide converted to TiO_2 and 0.05 to 0.85 mol % manganese oxide converted to MnO.
2. The dielectric ceramic composition as in claim 1 comprising a main component including 60.00 to 70.00mol % said magnesium oxide converted to MgO, 29.60 to 39.90mol % said titanium oxide converted to TiO_2 and 0.20 to 0.60 mol % said manganese oxide converted to MnO.
3. The dielectric ceramic composition as in claim 1, as subcomponent, further comprising, with respect to entire dielectric ceramic composition, 0.00 to 0.20 mol% of at least any one of vanadium oxide, yttrium oxide, ytterbium oxide or holmium oxide converted to V_2O_5 ,Y_2O_3, Yb_2O_3 and Ho_2O_3 respectively.
4. The dielectric ceramic composition as in claim 3 comprising, with respect to entire dielectric ceramic composition, 0.00 to 0.05 mol% of at least any one of said vanadium oxide, yttrium oxide, ytterbium oxide or holmium oxide converted to V_2O_5 ,Y_2O_3, Yb_2O_3 and Ho_2O_3 respectively.
5. A process of manufacturing dielectric ceramic composition as in any of the claim 1 or 3, comprising the steps of preparing source material for said dielectric ceramic composition and firing said source material under the temperature of 1300℃ or less to obtain said dielectric ceramic composition.
6. The process of manufacturing dielectric ceramic composition as in claim 5 characterized in that said source material is anneal treated after being fired in reducing atmosphere.
7. An electronic device comprising dielectric layers, characterized in that said

dielectric layers are composed of the dielectric ceramic composition as in any of claim 1 or 3.

8. An electronic device wherein inner electrodes and dielectric layers stacked alternately, characterized in that said dielectric layers are composed of the dielectric ceramic composition as in any of the claim1 or 3.

9. The electronic device as in claim 8, wherein said internal electrode at least includes nickel.

10. A process of manufacturing electronic device as in any of claim 8 or 9, characterized in cofiring internal electrode and dielectric layers under the temperature of 1300℃ or less.

11. The process of manufacturing the electronic device as in claim 8 characterized in that said dielectric ceramic composition is anneal treated after being fired in reducing atmosphere.